PRINTER RUSH
(PTO ASSISTANCE)

Application :	09/536,037	**Examiner :**	Wilczewski	**GAU :**	2822
From:	MR	**Location:**	(IDC) FMF FDC	**Date:**	07-23-05
		Tracking #:	0595912	Week Date:	05-31-05

DOC CODE	DOC DATE	MISCELLANEOUS
☑ 1449	03-24-05	☐ Continuing Data
☐ IDS		☐ Foreign Priority
☐ CLM		☐ Document Legibility
☐ IIFW		☐ Fees
☐ SRFW		☐ Other
☐ DRW		
☐ OATH		
☐ 312		
☐ SPEC		

[RUSH] **MESSAGE:** Please supply clear copy of PTO-1449 dated 03-24-05 pg. 5. Copy in that file is illegible.

Thank you,
MR

[XRUSH] **RESPONSE:** corrected

See Attachments

INITIALS: KP

NOTE: This form will be included as part of the official USPTO record, with the Response document coded as XRUSH.

REV 10/04

FACSIMILE COVER PAGE

TO:	**Kay Pinkney**	**FAX NO:**	**(703) 308-6642**
FROM:	**Racquel M. Esplin** **Assistant to James E. Lake**		
DATE:	**July 28, 2005**	**NO. OF PAGES:**	**3**
OUR FILE:	**MI22-1398**	**APPLICATION NO.:**	**09/536,037**

SUBJECT/MESSAGE:

Per your request please find enclosed a copy of the PTO-1449, page 5. The document has been enlarged for legibility and has extended onto a second page. If you have any questions please don't hesitate to contact me.

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-1398	SERIAL NO. 09/536,037
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)	APPLICANT Weimin (Michael) Li et al.	
	FILING DATE March 27, 2000	GROUP 2822

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

Examiner's Initials				Name			
	AA			TEXT: Jenkins, F. et al., AFundamentals of Optics@, Properties of Light, pp. 9-10. (No date)			
	AB			TEXT: Wolf, S. et al., ASilicon Processing for the VLSI Era@, Vol. 1, pp. 437-441. (No date)			
	AC			D.R. McKenzie et al., ANew Technology for PACVD™", Surface and Coatings Technology, 82 (1996), pp. 326-333.			
	AD			S. McClatchie et al.; "Low Dielectric Constant Flowfill7 Technology For IMD Applications"; undated; 7 pages			
	AE			K. Beekmann et al.; "Sub-micron Gap Fill and In-Situ Planarisation using FlowfillK Technology"; October 1995; pp. 1-7			
	AF			A. Kiermasz et al.; "Planarisation for Sub-Micron Devices Utilising a New Chemistry"; Electrotech, February 1995; 2 pages			
	AG			IBM Technical Disclosure Bulletin ALow-Temperature Deposition of SiO2, Si3N4 or SiO2-Si3N4,@ Vol. 28, No. 9, p. 4170, Feb. 1986.			
	AH			ARTICLE: Bencher, C. et al., ADielectric antireflective coatings for DUV lithography@, Solid State Technology (March 1997), pp.109-114.			
	AI			Noboru Shibata, APlasma-Chemical Vapor-Deposited Silicon Oxide/Silicon Oxynitride Double-Layer Antireflective Coating for Solar Cells@, Japanese Journal of Applied Physics, Vol. 30, No. 5, May 1991, pp. 997-1001.			
	AJ			Ralls, Kenneth M., AIntroduction to Materials Science and Engineering@, John Wiley & Sons, 8 1976, pp. 312-313			
	AK			Ravi K. Laxman, ASynthesizing Low-k CVD Materials for Fab Use@, Semiconductor International, Nov. 2000, 10 pps.			
	AL			Anonymous, ANew gas helps make faster IC=s, Machine Design Cleveland, 8 Penton Media, Inc., November 4, 1999, pp. 118			
	AM			Lobada et al, AUsing Trimethylsilane to Improve Safety Throughput and Versatility in PECVD Processes@, 4th International Symposium on Silicon Nitride and Silicon Dioxide Thin Insulating Films, The Electrochemical Society, Abstract No. 358, p. 454, May 1997.			
	AN			ARTICLE: Dammel, R. R. et al., ADependence of Optical Constants of AZ7 BARLiJ Bottom Coating on Back Conditions@, SPIE Vol. 3049 (1997), pp. 963-973.			
	AO			TEXT: Heavens, O. S., AOptical Properties of Thin Solid Films@, pp. 48-49.			

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

Examiner's Initials				Name			
	AP			Withmall, R. et al., AMatrix Reactions of Methyisilanes and Oxygen Atoms@, Phys. Chem 1988, pp. 594-602.			
	AQ			Weidman, T. et al., ANew photodefinable glass etch masks for entirely dry photolithography: Plasma deposited orarganosilicon hydride polymers@, Appl. Phys. Lett 1-25-93, pp. 372-374.			
	AR			Weidman, et al., AAll Dry Lithography: Applications of Plasma Polymerized Methylsilane as a Single Layer Resist and Silicon Dioxide Precursor@, Journal of Photopolymer Science and Technology, V. 8, #4, 1995, pp. 679-686.			
	AS			Joubert et al., AApplication of Plasma Polymerized Methylsilane in an all dry resist process for 193 and 248 nm Lithography@, Microelectronic Engineering 30 (1996), pp. 275-278.			
	AT			Joshi, A.M. et al., APlasma Deposited Organosilicon Hydride Network Polymers as Versatile Resists for Entirely Dry Mid-Deep UV Photolithography, SPIE Vol. 1925, pp. 709-720.			
	AU			Matsuura, M. et al., AHighly Reliable Self-Planarizing Low-k Intermetal Dieletric for Sub-quarter Micron Interconnects@, IEEE 1997, pp. 785-788.			
	AV			Horie, O. et al., AKinetics and Mechanism of the Reactions of ..., J. Phys. Chem 1991, 4393-4400.			

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